

## A SINGLE RIE PROCESS FOR MIMCAP TOP AND BOTTOM PLATES

### ABSTRACT

5        A method of forming MIM capacitor top (16) and  
bottom (12) plates, using a first and second resist  
(18/20) and a single RIE process. A first conductive  
layer (12) is deposited over a substrate (10). An  
insulating layer (14) is deposited over the first  
10    conductive layer (12). A second conductive layer (16) is  
deposited over the insulating layer (14). A first resist  
(18) is deposited over the second conductive layer (16),  
and the first resist (18) is patterned. A second resist  
(20) is deposited over the first resist (18) and  
15    patterned. The first and second resist (18/20) patterns  
are simultaneously transferred to the first and second  
conductive layers (12) and (16), respectively, by  
exposure to a single reactive ion etch (RIE) process.